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June 2014

# **FQA70N15**

### N-Channel QFET® MOSFET

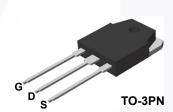
**150 V, 70 A, 28 m**Ω

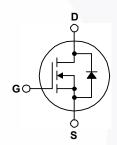
### Description

This N-Channel enhancement mode power MOSFET is produced Fairchild using Semiconductor's proprietary planar stripe and DMOS technology. This advanced MOSFET technology has been especially tailored to reduce on-state resistance, and to provide superior switching performance and high avalanche energy strength. These devices are suitable for switched • 175°C Maximum Junction Temperature Rating mode power supplies, audio amplifier, DC motor control, and variable switching power applications.

#### **Features**

- 70 A, 100 V,  $R_{DS(on)}$  = 28 m $\Omega$  (Max)@ $V_{GS}$  = 10 V,  $I_D$  = 35 A
- Low Gate Charge (Typ. 135 nC)
- Low Crss (Typ.135 pF)
- · 100% Avalanche Tested





### Absolute Maximum Ratings T<sub>C</sub> = 25°C unless otherwise noted

Symbol	Parameter		FQA70N15	Unit
$V_{DSS}$	Drain-Source Voltage		150	V
I <sub>D</sub>	Drain Current - Continuous (T <sub>C</sub> = 25°	C)	70	Α
	- Continuous (T <sub>C</sub> = 100°C)		50	Α
I <sub>DM</sub>	Drain Curent - Pulsed	(Note 1)	280	А
V <sub>GSS</sub>	Gate-Source Voltage		± 25	V
E <sub>AS</sub>	Single Pulsed Avalanche Energy	(Note 2)	1000	mJ
I <sub>AR</sub>	Avalanche Current	(Note 1)	70	Α
E <sub>AR</sub>	Repetitive Avalanche Energy	(Note 1)	33	mJ
dv/dt	Peak Diode Recovery dv/dt	(Note 3)	6.0	V/ns
$P_{D}$	Power Dissipation (T <sub>C</sub> = 25°C)		330	W
	- Derate above 25°C		2.2	W/°C
T <sub>J</sub> , T <sub>STG</sub>	Operating and Storage Temperature Range		-55 to +175	°C
T <sub>L</sub>	Maximum lead temperature for soldering purposes, 1/8" from case for 5 seconds		300	°C

#### **Thermal Characteristics**

Symbol	Parameter	FQA70N15	Unit	
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case, Max.	0.45	°C/W	
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient, Max.	40	°C/W	

### **Package Marking and Ordering Information**

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FQA70N15	FQA70N15	TO-3PN	-	-	30

### **Flectrical Characteristics**

Symbol	Parameter	Test Conditions	Min	Тур	Max	Unit
Off Cha	aracteristics					
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$	150			V
ΔBV <sub>DSS</sub> / ΔT <sub>J</sub>	Breakdown Voltage Temperature Coefficient	$I_D$ = 250 $\mu$ A, Referenced to 25°C		0.15		V/°C
I <sub>DSS</sub>	7 0 1 1/1 1 2 1 0 1	V <sub>DS</sub> = 150 V, V <sub>GS</sub> = 0 V			1	μΑ
	Zero Gate Voltage Drain Current	V <sub>DS</sub> = 120 V, T <sub>C</sub> = 150°C			10	μΑ
I <sub>GSSF</sub>	Gate-Body Leakage Current, Forward	V <sub>GS</sub> = 25 V, V <sub>DS</sub> = 0 V			100	nA
I <sub>GSSR</sub>	Gate-Body Leakage Current, Reverse	V <sub>GS</sub> = -25 V, V <sub>DS</sub> = 0 V			-100	nA
On Cha	aracteristics					
V <sub>GS(th)</sub>	Gate Threshold Voltage	$V_{DS} = V_{GS}$ , $I_{D} = 250 \mu A$	2.0		4.0	V
R <sub>DS(on)</sub>	Static Drain-Source On-Resistance	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 35 A		0.023	0.028	Ω
g <sub>FS</sub>	Forward Transconductance	V <sub>DS</sub> = 40 V, I <sub>D</sub> = 35 A		48		S
C <sub>iss</sub>	ic Characteristics Input Capacitance	V <sub>DS</sub> = 25 V, V <sub>GS</sub> = 0 V,		4150	5400	pF
C <sub>oss</sub>	Output Capacitance	f = 1.0 MHz		840	1100	pF
C <sub>rss</sub>	Reverse Transfer Capacitance			135	175	pF
Switchi	ing Characteristics					
t <sub>d(on)</sub>	Turn-On Delay Time	V 75.V L 70.A		60	130	ns
t <sub>r</sub>	Turn-On Rise Time	$V_{DD} = 75 \text{ V}, I_{D} = 70 \text{ A},$ $R_{G} = 25 \Omega$		420	850	ns
t <sub>d(off)</sub>	Turn-Off Delay Time	11G - 23 22		340	690	ns
t <sub>f</sub>	Turn-Off Fall Time	(Note 4)		290	590	ns
Qg	Total Gate Charge	V <sub>DS</sub> = 120 V, I <sub>D</sub> = 70 A,	/	135	175	nC
$Q_{gs}$	Gate-Source Charge	V <sub>GS</sub> = 10 V		25		nC
Q <sub>gd</sub>	Gate-Drain Charge	(Note 4)		65		nC
Drain-S	Source Diode Characteristics ar	nd Maximum Ratings				
I <sub>S</sub>	Maximum Continuous Drain-Source Diode Forward Current				70	Α
I <sub>SM</sub>	Maximum Pulsed Drain-Source Diode Forward Current				280	Α
V <sub>SD</sub>	Drain-Source Diode Forward Voltage	V <sub>GS</sub> = 0 V, I <sub>S</sub> = 70 A			1.5	V
t <sub>rr</sub>	Reverse Recovery Time	V <sub>GS</sub> = 0 V, I <sub>S</sub> = 70 A,		150		ns
Q <sub>rr</sub>	Reverse Recovery Charge	dI <sub>F</sub> / dt = 100 A/μs		0.67		μС

- **Notes:**1. Repetitive Rating : Pulse width limited by maximum junction temperature 2. L = 0.34mH,  $I_{AS} = 70$ A,  $V_{DD} = 25$ V,  $R_{C} = 25$   $\Omega$ , Starting  $T_{J} = 25$ °C 3.  $I_{SD} \le 70$ A, di/dt  $\le 300$ A/ $\mu$ s,  $V_{DD} = BV_{DSS}$ , Starting  $T_{J} = 25$ °C 4. Essentially independent of operating temperature

### **Typical Characteristics**

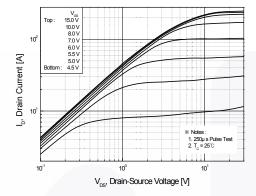


Figure 1. On-Region Characteristics

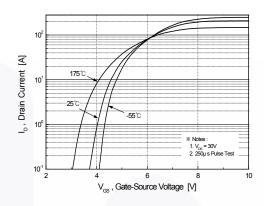


Figure 2. Transfer Characteristics

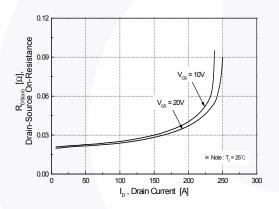


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

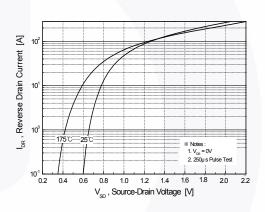


Figure 4. Body Diode Forward Voltage Variation vs. Source Current

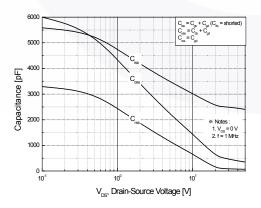


Figure 5. Capacitance Characteristics

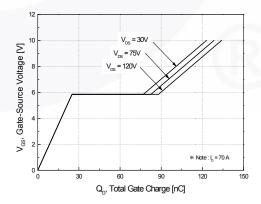


Figure 6. Gate Charge Characteristics

### Typical Characteristics (Continued)

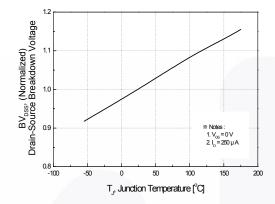


Figure 7. Breakdown Voltage Variation vs. Temperature

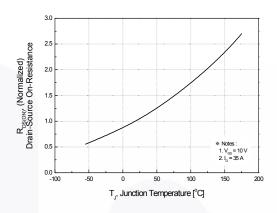


Figure 8. On-Resistance Variation vs. Temperature

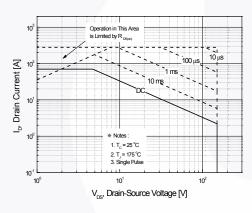


Figure 9. Maximum Safe Operating Area

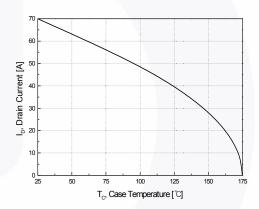


Figure 10. Maximum Drain Current vs. Case Temperature

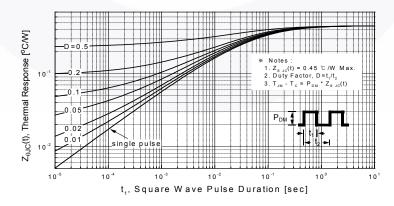


Figure 11. Transient Thermal Response Curve



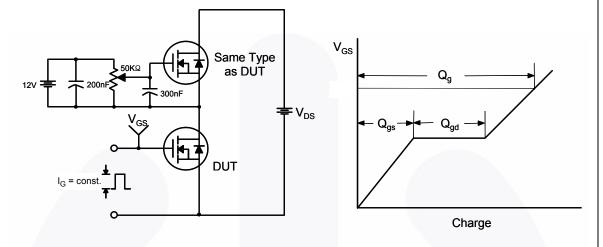


Figure 13. Resistive Switching Test Circuit & Waveforms

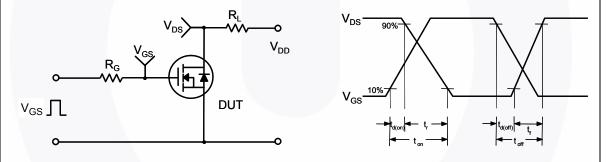
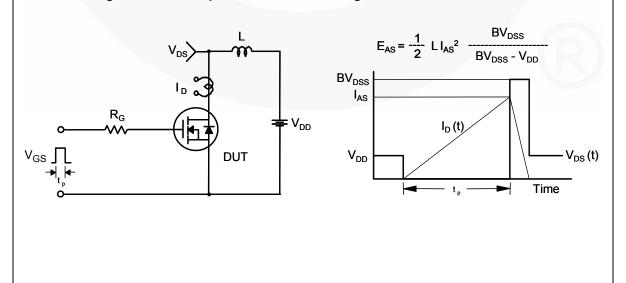
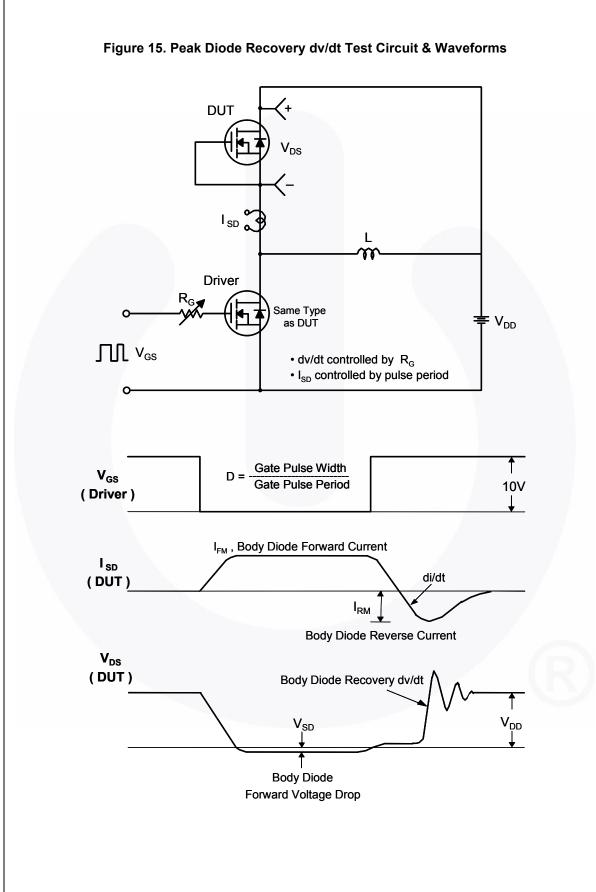


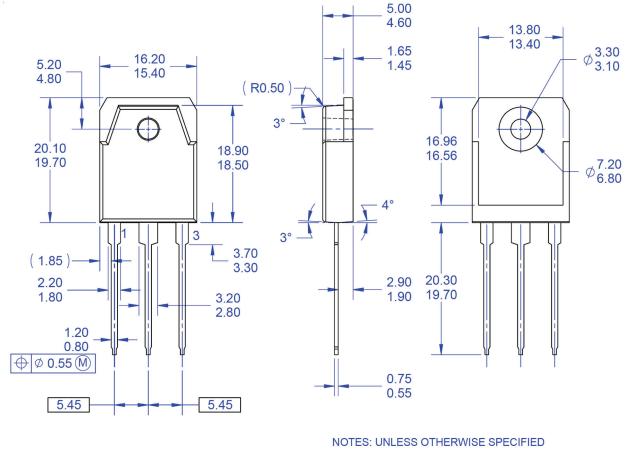
Figure 14. Unclamped Inductive Switching Test Circuit & Waveforms

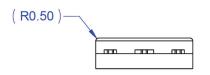




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#### **Mechanical Dimensions**





- A) THIS PACKAGE CONFORMS TO EIAJ SC-65 PACKAGING STANDARD.
- ALL DIMENSIONS ARE IN MILLIMETERS.
  DIMENSION AND TOLERANCING PER
- ASME14.5-2009.
- D) DIMENSIONS ARE EXCLUSSIVE OF BURRS, MOLD FLASH, AND TIE BAR EXTRUSSIONS. DRAWING FILE NAME: TO3PN03AREV1.
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#### Figure 16. TO3PN, 3-Lead, Plastic, EIAJ SC-65

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